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AN 1998-193647 [17] WPIDS
DNN N1998-153188 DNC C1998-062084
TI **Copper** alloy for electronic devices - comprises specified weights of **Zinc**, **Lead**, Tellurium and other elements with the residue being **copper**.
DC L03 M26 U11 V04 X12
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CYC 3
PI WO 9810105 A1 19980312 (199817)* JA 42p <--
W:--KR-US
JP 10081926 A 19980331 (199823) 5p <--
JP 10280072 A 19981020 (199901) 6p <--
JP 11036027 A 19990209 (199916) 6p <--
JP 11036028 A 19990209 (199916) 7p <--
JP 3014672 B2 20000228 (200015) 7p <--
JP 3014673 B2 20000228 (200015) 8p <--
ADT WO 9810105 A1 WO 1997-JP3080 19970903; JP 10081926 A JP 1996-235086 19960905; JP 10280072 A JP 1997-83761 19970402; JP 11036027 A JP 1998-135181 19980518; JP 11036028 A JP 1998-135182 19980518; JP 3014672
B2 JP 1998-135181 19980518; JP 3014673 B2 JP 1998-135182 19980518
FDT JP 3014672 B2 Previous Publ. JP 11036027; JP 3014673 B2 Previous Publ. JP 11036028
PRAI JP 1997-126538 19970516; JP 1996-235086 19960905; JP 1997-83761 19970402; JP 1997-126537 19970516
AB WO 9810105 A UPAB: 19980428
Copper alloy for electronic devices, comprising 5-42% by weight of **Zn**, at least 1 of elements selected from the group consisting of **Sn**, **Si**, **Al**, **Ni**, **Mn**, **Ti**, **Zr**, **In**, **Mg**, 0.005-0.5% by weight of **Pb**, and 0.005-0.5% by weight of **Te** in a total amount of 0.1-3% by weight, at least 1 of elements selected from the group consisting of **Bi**, **Ca**, **Sr** and **Ba** in a total amount of 0.005-3% by weight, the residue being **copper** and unavoidable impurities. The **copper** alloy containing 10-35% by weight of **Zn**, 0.1-2% by weight of **Sn**, the residue being **copper** and unavoidable impurities and having a crystal particle size of 5-35 μ m, is particularly suited for a material for **lead** frames for semiconductor devices.
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